

CD54HC245, CD54HCT245, CD74HC245, CD74HCT245

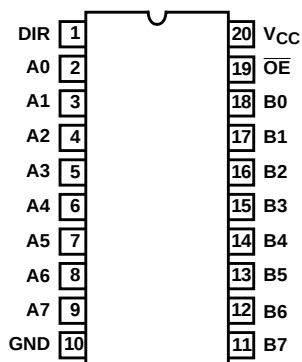
**High Speed CMOS Logic Octal-Bus Transceiver,
Three-State, Non-Inverting**

Features

- Buffered Inputs
- Three-State Outputs
- Bus Line Driving Capability
- Typical Propagation Delay (A to B, B to A) 9ns at V_{CC}
= 5V, $C_L = 15\text{pF}$, $T_A = 25^\circ\text{C}$
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC}
at $V_{CC} = 5\text{V}$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 $V_{IL} = 0.8\text{V}$ (Max), $V_{IH} = 2\text{V}$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu\text{A}$ at V_{OL} , V_{OH}

Pinout

CD54HC245, CD54HCT245, CD74HC245, CD74HCT245
(CERDIP, PDIP, SOIC)
TOP VIEW



CD54HC245, CD54HCT245, CD74HC245, CD74HCT245

Description

The Harris CD54HC245, CD54HCT245, and CD74HC245, CD74HCT245 are high-speed octal three-state bidirectional transceivers intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation while driving large bus capacitances. They provide the low power consumption of standard CMOS circuits with speeds and drive capabilities comparable to that of LSTTL circuits.

The CD54HC245, CD54HCT245, CD74HC245 and CD74HCT245 allow data transmission of the B bus or from the B bus to the A bus. The logic level at the direction input (DIR) determines the direction. The output enable input ($\overline{OE}$), when high, puts the I/O ports in the high-impedance state.

The HC/HCT245 is similar in operation to the HC/HCT640

and the HC/HCT643.

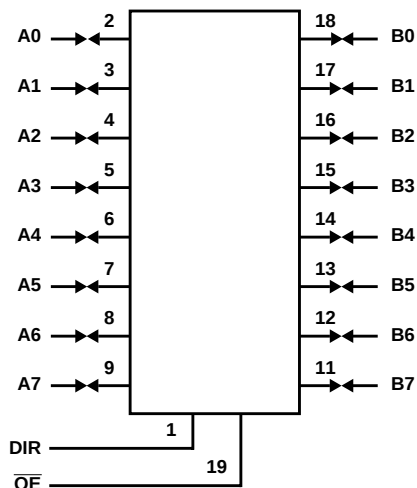
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD54HC245F	-55 to 125	20 Ld CERDIP	F20.3
CD54HCT245F	-55 to 125	20 Ld CERDIP	F20.3
CD74HC245E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT245E	-55 to 125	20 Ld PDIP	E20.3
CD74HC245M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT245M	-55 to 125	20 Ld SOIC	M20.3

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Functional Diagram



TRUTH TABLE

CONTROL INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B Data to A Bus
L	H	A Data to B Bus
H	X	Isolation

H = High Level, L = Low Level, X = Irrelevant

To prevent excess currents in the High-Z (Isolation) modes all I/O terminals should be terminated with 10k Ω to 1M Ω resistors.

CD54HC245, CD54HCT245, CD74HC245, CD74HCT245

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} ($^{\circ}\text{C/W}$)	θ_{JA} ($^{\circ}\text{C/W}$)
PDIP Package	125	N/A
SOIC Package	120	N/A
CERDIP Package	100	40
Maximum Junction Temperature	150 $^{\circ}\text{C}$	
Maximum Storage Temperature Range	-65 $^{\circ}\text{C}$ to 150 $^{\circ}\text{C}$	
Maximum Lead Temperature (Soldering 10s)	300 $^{\circ}\text{C}$	
(SOIC - Lead Tips Only)		

Operating Conditions

Temperature Range, T_A	-55 $^{\circ}C$ to 125 $^{\circ}C$
Supply Voltage Range, V_{CC}	
HC Types	.2V to 6V
HCT Types	.4.5V to 5.5V
DC Input or Output Voltage, V_I , V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
-			-	-	-	-	-	-	-	-	V	
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
-			-	-	-	-	-	-	-	-	V	
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

CD54HC245, CD54HCT245, CD74HC245, CD74HCT245

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5	-	±10	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
An or Bn	0.4
OE	1.5
DIR	0.9

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360μA max at 25°C.

CD54HC245, CD54HCT245, CD74HC245, CD74HCT245

Switching Specifications $C_L = 50\text{pF}$, Input t_r , $t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Data to Output	t _{PHL} , t _{PLH}	C _L = 50pF	2	-	-	110	-	140	-	165	ns
			4.5	-	-	22	-	28	-	33	ns
		C _L = 15pF	5	-	9	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	19	-	24	-	28	ns
Output Disable to Output	t _{PHL} , t _{PLH}	C _L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	26	-	33	-	38	ns
Output Enable to Output	t _{PHL} , t _{PLH}	C _L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	26	-	33	-	38	ns
Output Transition Time	t _{THL} , t _{TLH}	C _L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C _{IN}	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C _O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C _{PD}	-	5	-	53	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Data to Output	t _{PHL} , t _{PLH}	C _L = 50pF	4.5	-	-	26	-	33	-	39	ns
		C _L = 15pF	5	-	10	-	-	-	-	-	ns
Output Disable to Output	t _{PHL} , t _{PLH}	C _L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
Output Enable to Output	t _{PHL} , t _{PLH}	C _L = 50pF	4.5	-	-	32	-	40	-	48	ns
		C _L = 15pF	5	-	13	-	-	-	-	-	ns
Output Transition Time	t _{THL} , t _{TLH}	C _L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C _{IN}	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C _O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C _{PD}	-	5	-	55	-	-	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per channel.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

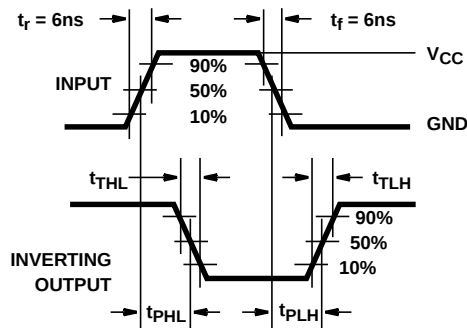


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

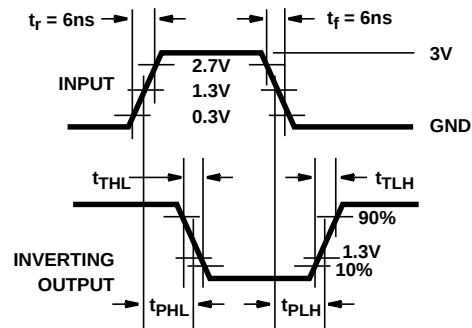


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

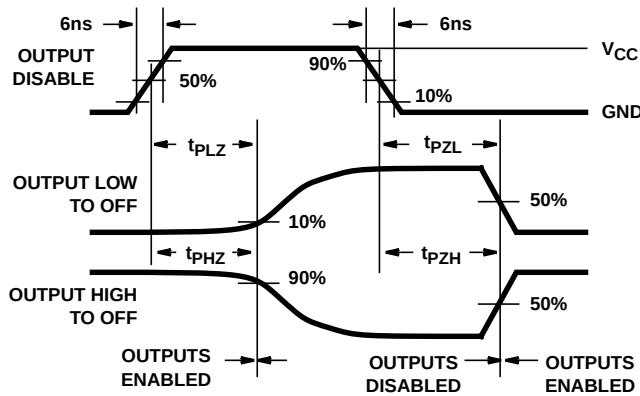


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

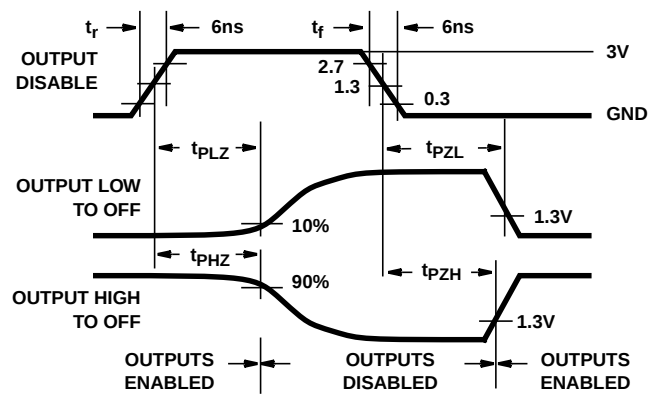
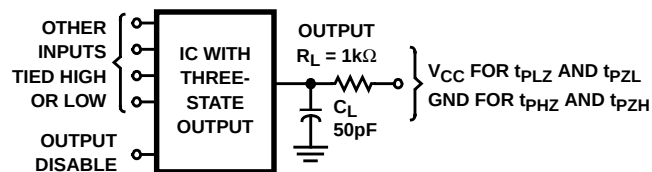


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.